

MOSFET

600V CoolMOS™ C7 Power Device

CoolMOS™ C7 is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies.

600V CoolMOS™ C7 series combines the experience of the leading SJ MOSFET supplier with high class innovation.

The 600V C7 is the first technology ever with $R_{DS(on)} \cdot A$ below $10\text{Ohm} \cdot \text{mm}^2$.

Features

- Suitable for hard and soft switching (PFC and high performance LLC)
- Increased MOSFET dv/dt ruggedness to 120V/ns
- Increased efficiency due to best in class FOM $R_{DS(on)} \cdot E_{oss}$ and $R_{DS(on)} \cdot Q_g$
- Best in class $R_{DS(on)}$ /package

Benefits

- Increased economies of scale by use in PFC and PWM topologies in the application
- Higher dv/dt limit enables faster switching leading to higher efficiency
- Enabling higher system efficiency by lower switching losses
- Increased power density solutions due to smaller packages
- Suitable for applications such as server, telecom and solar
- Higher switching frequencies possible without loss in efficiency due to low E_{oss} and Q_g

Potential applications

PFC stages and PWM stages (TTF, LLC) for high power/performance SMPS e.g. Computing, Server, Telecom, UPS and Solar.

Product validation

Fully qualified according to JEDEC for Industrial Applications

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.

Table 1 Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max}$	180	$m\Omega$
$Q_{g,typ}$	24	nC
$I_{D,pulse}$	45	A
$I_{D,continuous} @ T_j < 150^\circ\text{C}$	22	A
$E_{oss}@400\text{V}$	2.7	μJ
Body diode di/dt	350	$\text{A}/\mu\text{s}$

Type / Ordering Code	Package	Marking	Related Links
IPA60R180C7	PG-TO 220 FullPAK	60C7180	see Appendix A

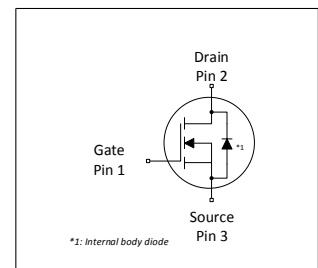


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1 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	9 5	A	$T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	45	A	$T_C=25^\circ\text{C}$
Avalanche energy, single pulse	E_{AS}	-	-	53	mJ	$I_D=3.3\text{A}$; $V_{DD}=50\text{V}$; see table 10
Avalanche energy, repetitive	E_{AR}	-	-	0.26	mJ	$I_D=3.3\text{A}$; $V_{DD}=50\text{V}$; see table 10
Avalanche current, single pulse	I_{AS}	-	-	3.3	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	120	V/ns	$V_{DS}=0\dots400\text{V}$
Gate source voltage (static)	V_{GS}	-20	-	20	V	static;
Gate source voltage (dynamic)	V_{GS}	-30	-	30	V	AC ($f>1\text{ Hz}$)
Power dissipation	P_{tot}	-	-	29	W	$T_C=25^\circ\text{C}$
Storage temperature	T_{stg}	-55	-	150	$^\circ\text{C}$	-
Operating junction temperature	T_j	-55	-	150	$^\circ\text{C}$	-
Mounting torque	-	-	-	50	Ncm	M2.5 screws
Continuous diode forward current	I_S	-	-	9	A	$T_C=25^\circ\text{C}$
Diode pulse current ²⁾	$I_{S,pulse}$	-	-	45	A	$T_C=25^\circ\text{C}$
Reverse diode dv/dt ³⁾	dv/dt	-	-	20	V/ns	$V_{DS}=0\dots400\text{V}$, $I_{SD}\leq 5.2\text{A}$, $T_j=25^\circ\text{C}$ see table 8
Maximum diode commutation speed	di/dt	-	-	350	A/ μs	$V_{DS}=0\dots400\text{V}$, $I_{SD}\leq 5.2\text{A}$, $T_j=25^\circ\text{C}$ see table 8
Insulation withstand voltage	V_{ISO}	-	-	2500	V	V_{rms} , $T_C=25^\circ\text{C}$, $t=1\text{min}$

¹⁾ Limited by $T_{j,max}$.

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Identical low side and high side switch

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	4.28	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	80	°C/W	leaded
Thermal resistance, junction - ambient for SMD version	R_{thJA}	-	-	-	°C/W	n.a.
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	-	-	260	°C	1.6mm (0.063 in.) from case for 10s

3 Electrical characteristics

at $T_j=25^\circ\text{C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	600	-	-	V	$V_{GS}=0V, I_D=1mA$
Gate threshold voltage	$V_{(GS)th}$	3	3.5	4	V	$V_{DS}=V_{GS}, I_D=0.26mA$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=600, V_{GS}=0V, T_j=25^\circ\text{C}$ $V_{DS}=600, V_{GS}=0V, T_j=150^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS}=20V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.155 0.346	0.180	Ω	$V_{GS}=10V, I_D=5.3A, T_j=25^\circ\text{C}$ $V_{GS}=10V, I_D=5.3A, T_j=150^\circ\text{C}$
Gate resistance	R_G	-	0.85	-	Ω	$f=1\text{MHz}$, open drain

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	1080	-	pF	$V_{GS}=0V, V_{DS}=400V, f=250\text{kHz}$
Output capacitance	C_{oss}	-	18	-	pF	$V_{GS}=0V, V_{DS}=400V, f=250\text{kHz}$
Effective output capacitance, energy related ¹⁾	$C_{o(er)}$	-	34	-	pF	$V_{GS}=0V, V_{DS}=0\dots400V$
Effective output capacitance, time related ²⁾	$C_{o(tr)}$	-	349	-	pF	$I_D=\text{constant}, V_{GS}=0V, V_{DS}=0\dots400V$
Turn-on delay time	$t_{d(on)}$	-	9.3	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=5.3A,$ $R_G=10\Omega$; see table 9
Rise time	t_r	-	7	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=5.3A,$ $R_G=10\Omega$; see table 9
Turn-off delay time	$t_{d(off)}$	-	50	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=5.3A,$ $R_G=10\Omega$; see table 9
Fall time	t_f	-	6	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=5.3A,$ $R_G=10\Omega$; see table 9

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{GS}	-	5	-	nC	$V_{DD}=400V, I_D=5.3A, V_{GS}=0$ to 10V
Gate to drain charge	Q_{gd}	-	8	-	nC	$V_{DD}=400V, I_D=5.3A, V_{GS}=0$ to 10V
Gate charge total	Q_g	-	24	-	nC	$V_{DD}=400V, I_D=5.3A, V_{GS}=0$ to 10V
Gate plateau voltage	$V_{plateau}$	-	5.0	-	V	$V_{DD}=400V, I_D=5.3A, V_{GS}=0$ to 10V

¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400V

²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400V

Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.9	-	V	$V_{GS}=0V, I_F=5.3A, T_j=25^{\circ}C$
Reverse recovery time	t_{rr}	-	280	-	ns	$V_R=400V, I_F=5.3A, di_F/dt=100A/\mu s$; see table 8
Reverse recovery charge	Q_{rr}	-	2.6	-	μC	$V_R=400V, I_F=5.3A, di_F/dt=100A/\mu s$; see table 8
Peak reverse recovery current	I_{rrm}	-	21	-	A	$V_R=400V, I_F=5.3A, di_F/dt=100A/\mu s$; see table 8

4 Electrical characteristics diagrams

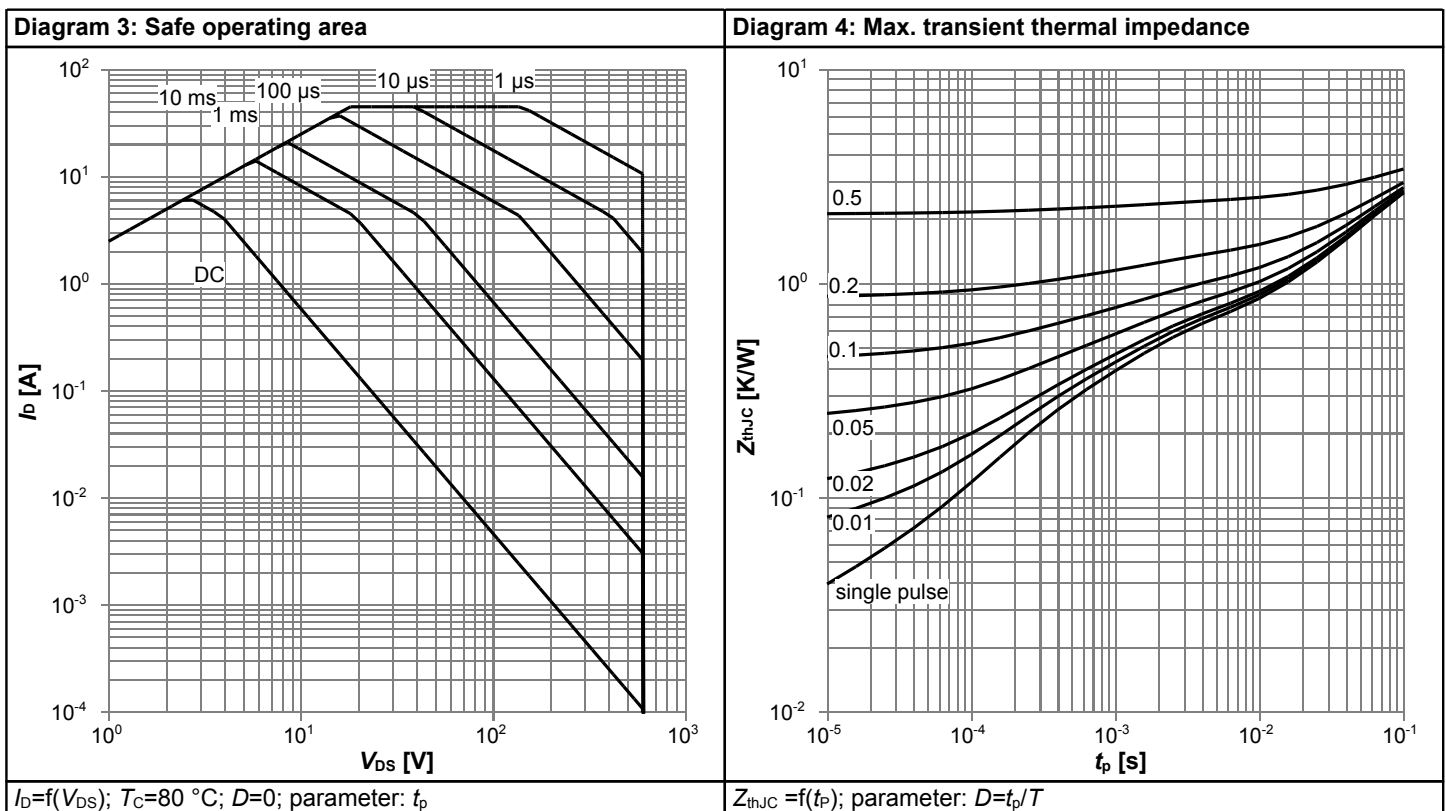
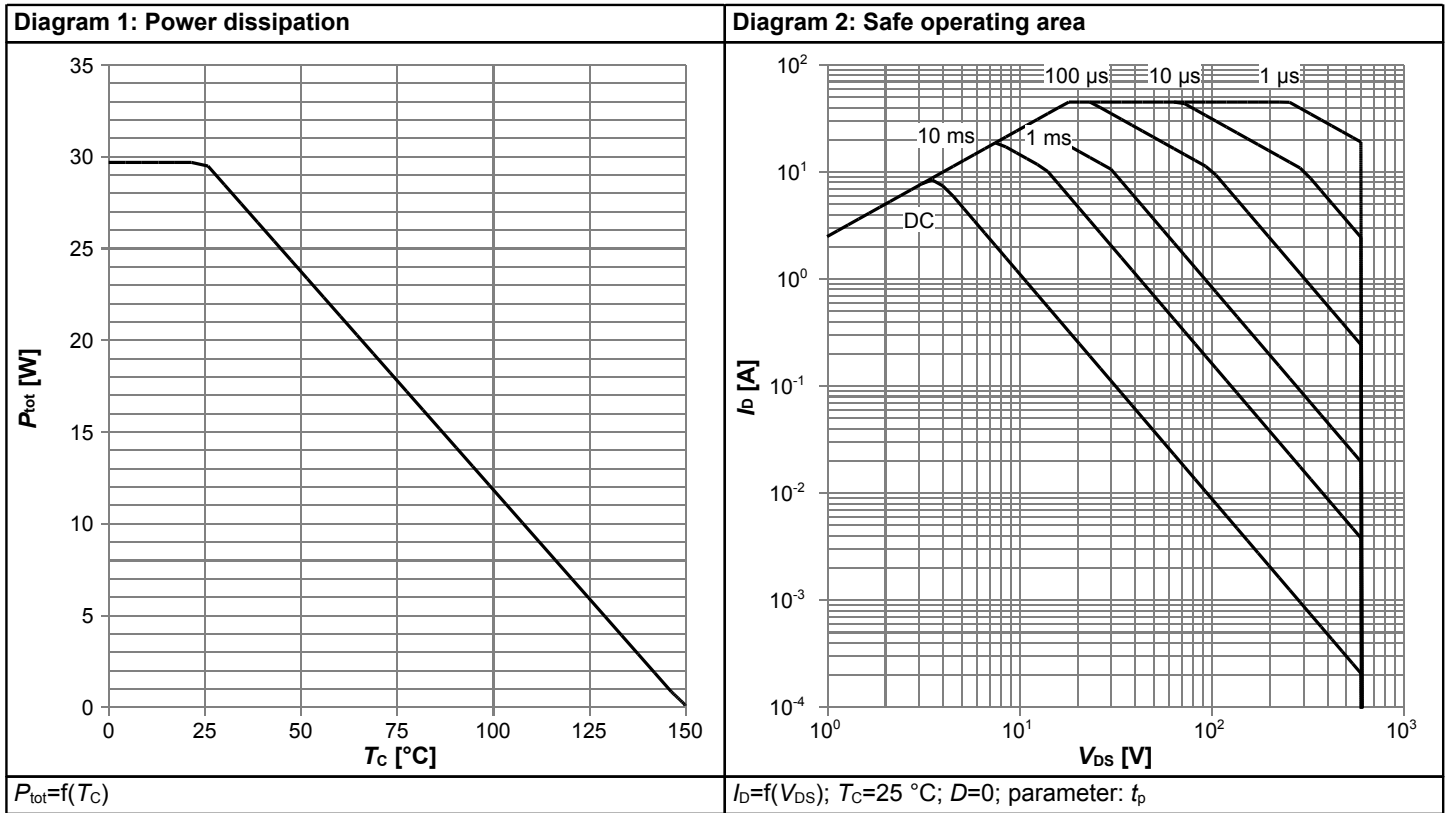
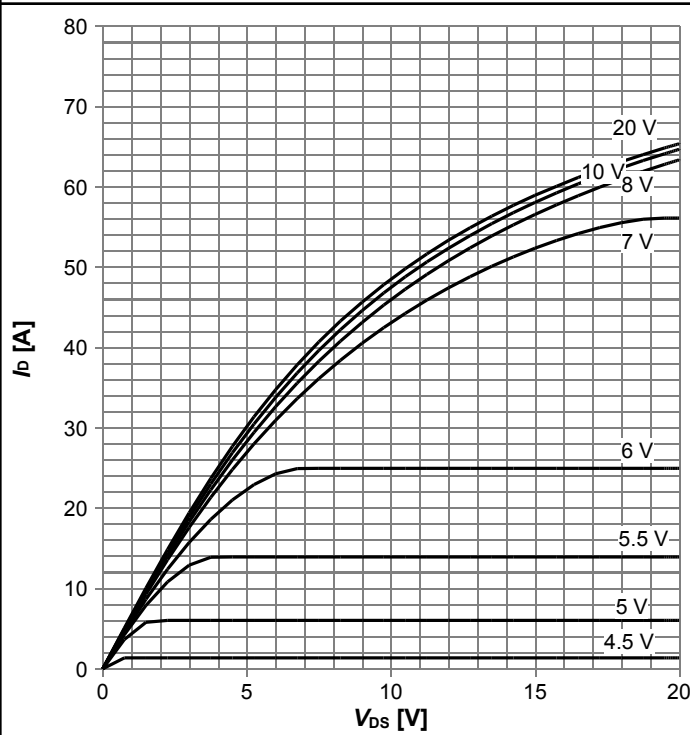
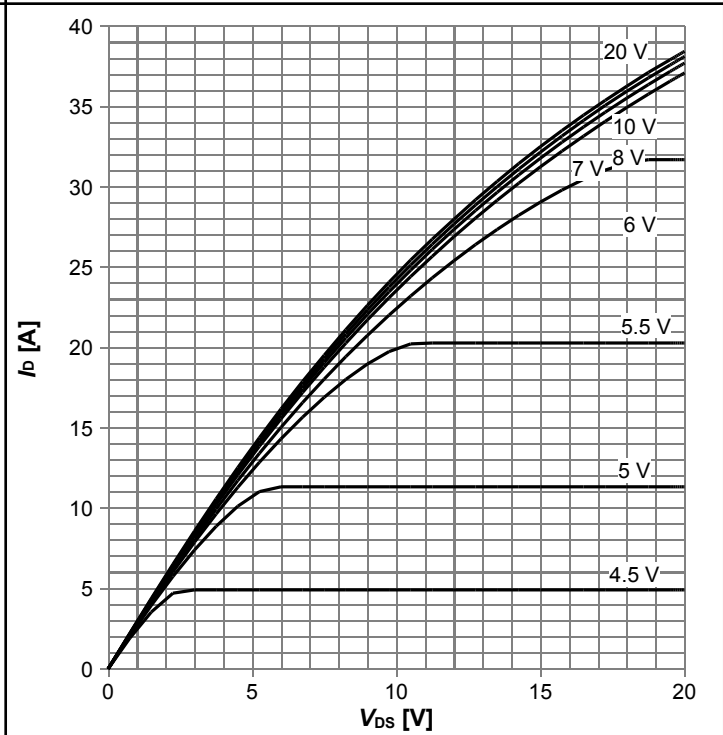


Diagram 5: Typ. output characteristics



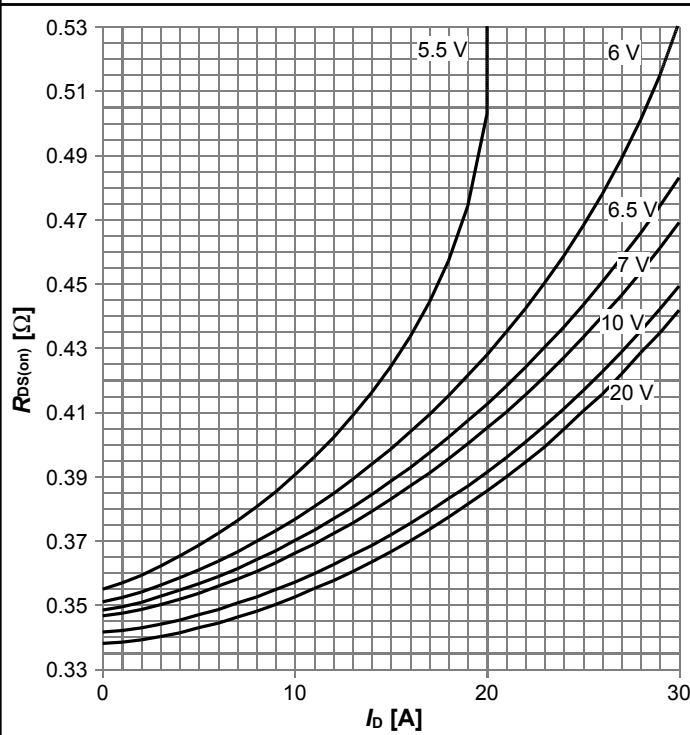
$I_D=f(V_{DS})$; $T_j=25\text{ °C}$; parameter: V_{GS}

Diagram 6: Typ. output characteristics



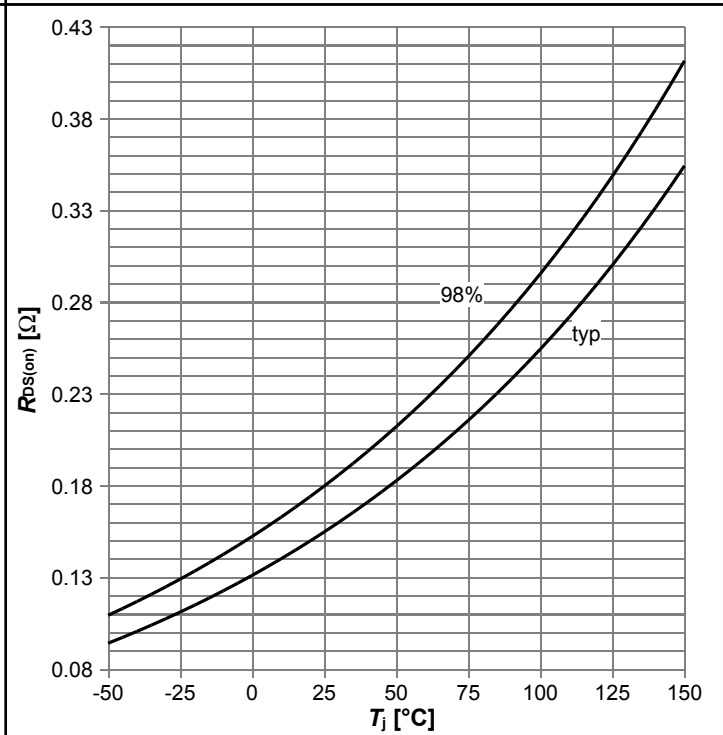
$I_D=f(V_{DS})$; $T_j=125\text{ °C}$; parameter: V_{GS}

Diagram 7: Typ. drain-source on-state resistance



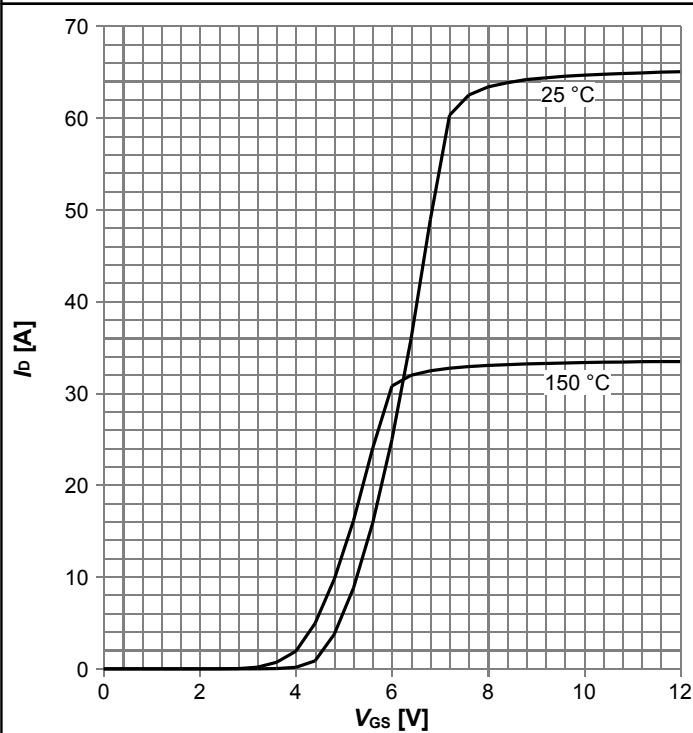
$R_{DS(on)}=f(I_D)$; $T_j=125\text{ °C}$; parameter: V_{GS}

Diagram 8: Drain-source on-state resistance



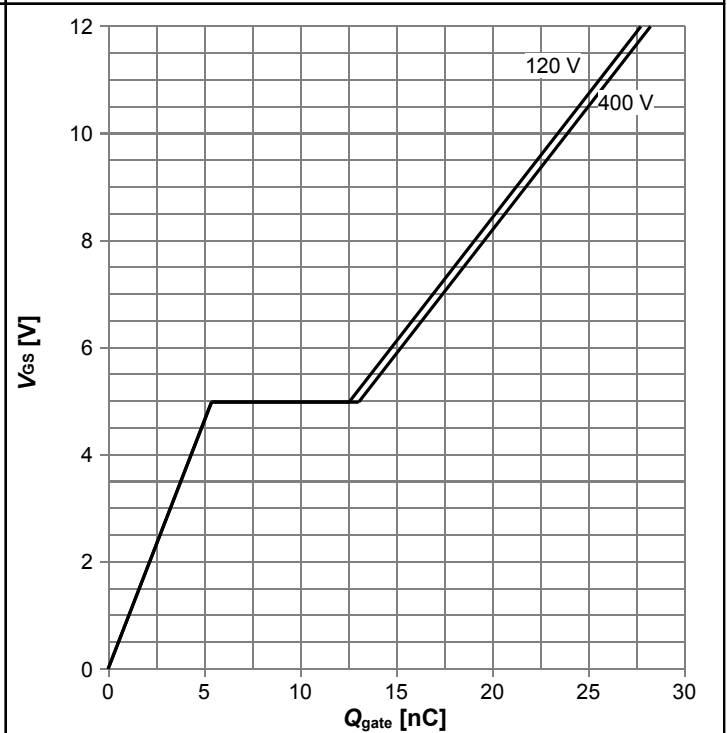
$R_{DS(on)}=f(T_j)$; $I_D=5.3\text{ A}$; $V_{GS}=10\text{ V}$

Diagram 9: Typ. transfer characteristics



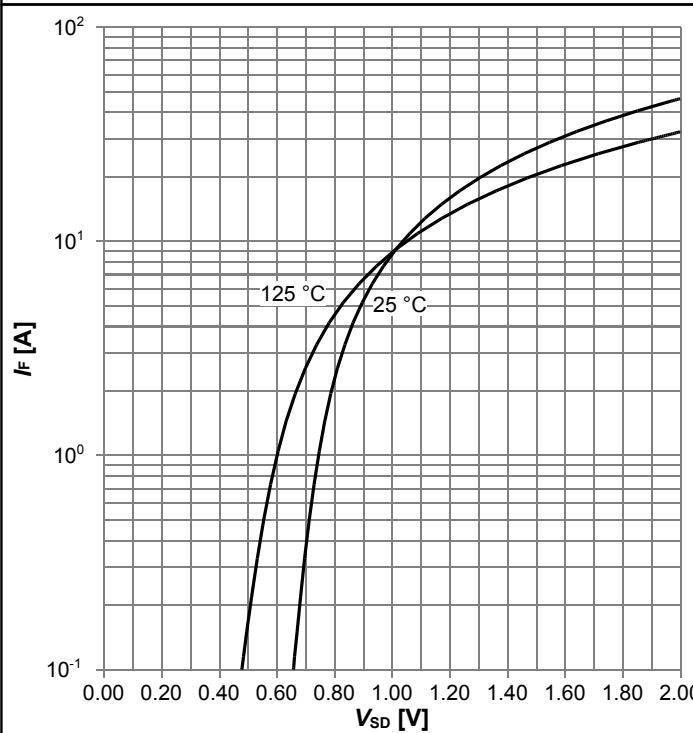
$I_D = f(V_{GS}); V_{DS} = 20V; \text{parameter: } T_j$

Diagram 10: Typ. gate charge



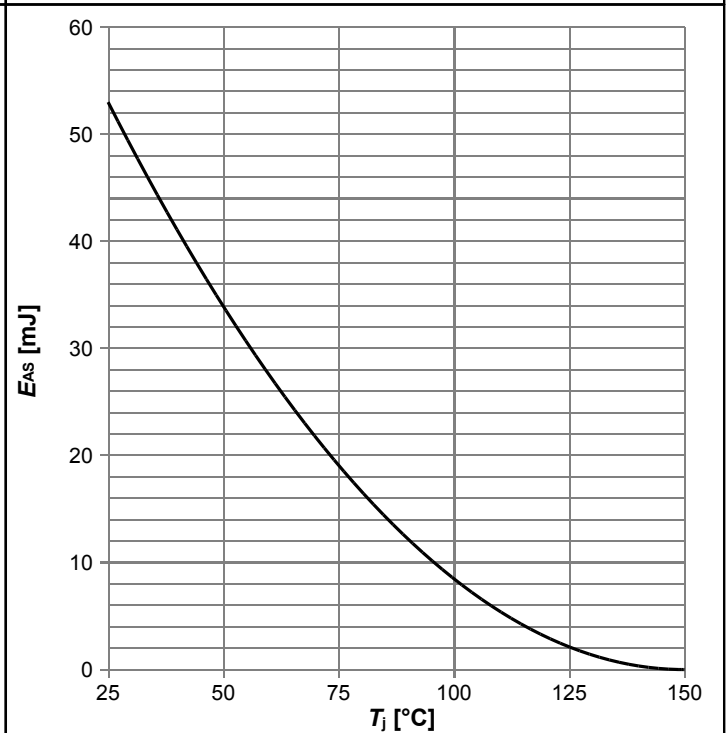
$V_{GS} = f(Q_{gate}); I_D = 5.3 \text{ A pulsed}; \text{parameter: } V_{DD}$

Diagram 11: Forward characteristics of reverse diode



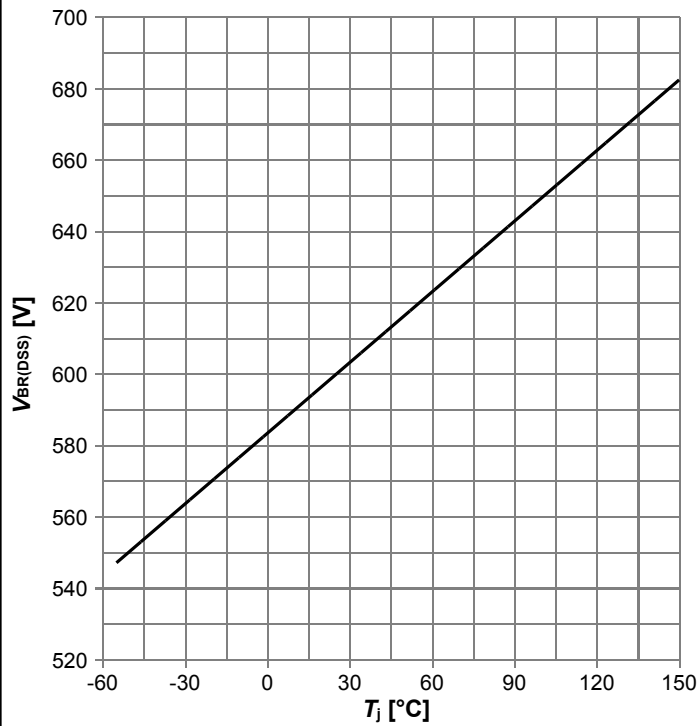
$I_F = f(V_{SD}); \text{parameter: } T_j$

Diagram 12: Avalanche energy



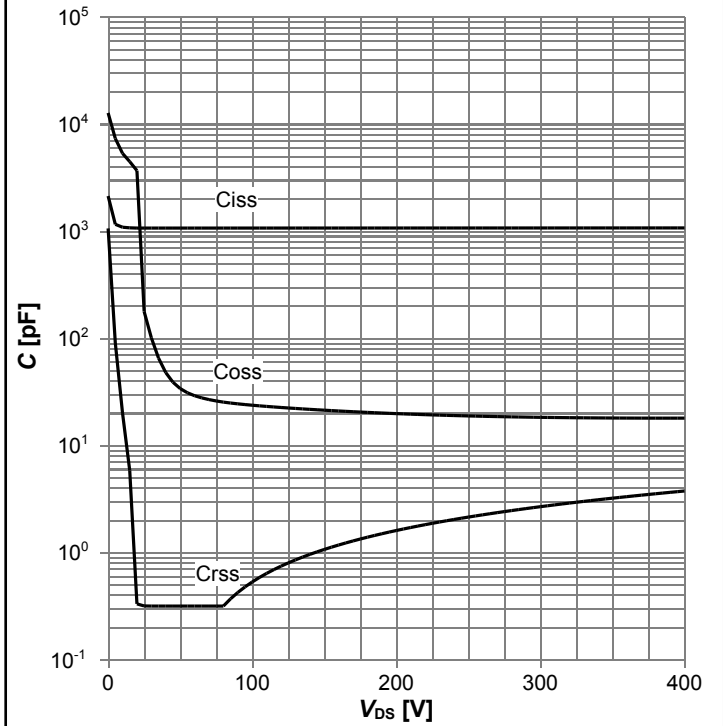
$E_{AS} = f(T_j); I_D = 3.3 \text{ A}; V_{DD} = 50 \text{ V}$

Diagram 13: Drain-source breakdown voltage



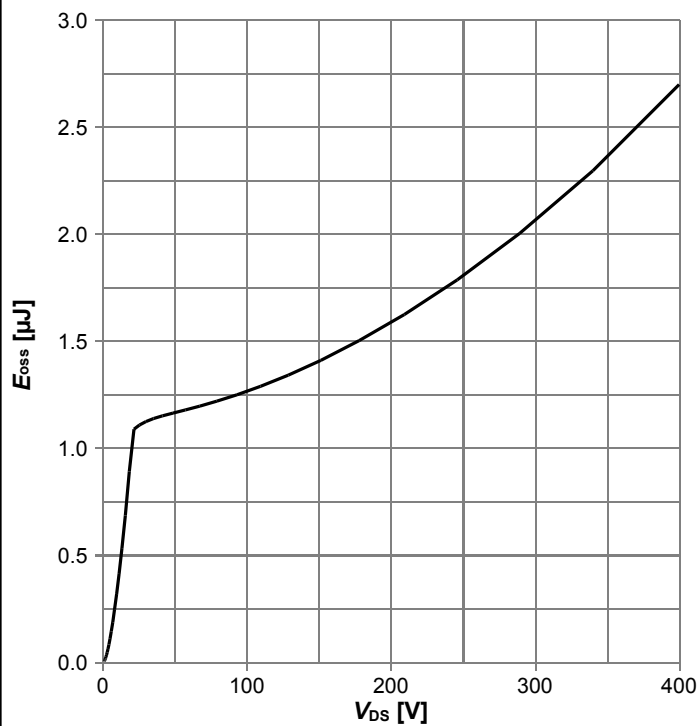
$V_{BR(DSS)}=f(T_j); I_D=1\text{ mA}$

Diagram 14: Typ. capacitances



$C=f(V_{DS}); V_{GS}=0\text{ V}; f=250\text{ kHz}$

Diagram 15: Typ. Coss stored energy



$E_{oss}=f(V_{DS})$

5 Test Circuits

Table 8 Diode characteristics



Table 9 Switching times



Table 10 Unclamped inductive load



6 Package Outlines



Figure 1 Outline PG-TO 220 FullPAK, dimensions in mm

7 Appendix A

Table 11 Related Links

- IFX CoolMOS™ C7 Webpage: www.infineon.com
- IFX CoolMOS™ C7 application note: www.infineon.com
- IFX CoolMOS™ C7 simulation model: www.infineon.com
- IFX Design tools: www.infineon.com

Revision History

IPA60R180C7

Revision: 2020-01-29, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2015-08-10	Release of final version
2.1	2020-01-29	Updated package drawing and product validation

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